IN THE SPECIFICATION

Please amend the third paragraph on page 3 as follows:

In accordance with an example reported in the above specification, it is shown that, for a 6-inch diameter wafer which is cleaned for 60 min with the Standard Cleaning - 1 (hereinafter referred to as "SC - 1"), which is made by using alkaline chemical liquid mainly containing NH_4OH, H_2O_2, and H_2O the surface density of particles having a diameter of not less than 0.13 μm is about 1200 counts/cm^2 when nitrogen is not doped, whereas it becomes about 1/20 of the above surface density when nitrogen is doped. In accordance with the description of the example, it is estimated that the surface density of particles having a size of not less than 0.13 μm is not more than 60 counts/cm^2. In recent years, a wafer having such a greater surface density as in this estimation can hardly be used as a wafer for manufacturing devices.